CULLADAT TECHNOLOCICAL UNIVERSITY

Su	uhiect	GUJARAT TECHNOLOGICAL UNIVERSITY BE - SEMESTER–VIII (OLD) - EXAMINATION – SUMMER 2017 Code:180802 Date:29/04/20	17		
Subject Name: VLSI Technologies Time:10:30 AM to 01:00 PM Total Marl Instructions:					
		Attempt all questions. Make suitable assumptions wherever necessary. Figures to the right indicate full marks.			
Q.1	(a)	Discuss VLSI design flow in brief.	07		
	(b)	Explain fabrication process of nMOS transistor with diagram.	07		
Q.2	(a)	Draw and explain Energy band diagram of a p-type silicon substrate.	07		
	(b)	Discuss basic steps of the LOCOS Process.	07		
		OR			
Q-2	(a)	What is enhancement-mode MOSFET and depletion-mode MOSFET? Explain in detail.	07		
	(b)	Draw and explain the structure of MOS.	07		
Q.3	(a)	Explain any one down scaling techniques for MOSFET.	07		
	(b)	Derive the equation of Threshold voltage of MOS Structure.	07		
OR					
Q.3	(a)	Explain Oxide-related Capacitances.	07		
	(b)	Explain the depletion load nMOS inverter and derive equation of critical voltage points VOH, VOL, VIL and VIH	07		
Q.4	(a)	Explain Noise immunity and noise margin using Inverter Example.	07		
	(b)	Explain Voltage Bootstrapping.	07		
OR					
Q.4	(a)	Explain CMOS Transmission Gates (TGs) in detail.	07		
	(b)	Explain basic principle of pass transistor with logic "1" transfer.	07		

	(b)	Give comparison between FPGA and CPLD.	07
Q.5	(a)	OR Explain Scan –based techniques in detail.	07
	(b)	Discuss Controllability and Observability.	07
